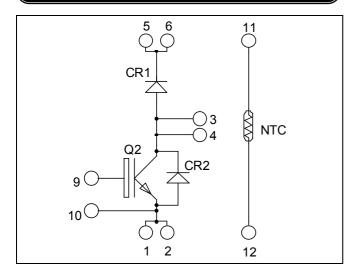
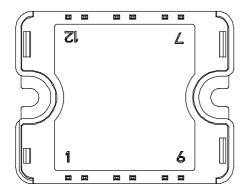


## Boost chopper Trench + Field Stop IGBT4 Power module







Pins 1/2; 3/4; 5/6 must be shorted together

#### **Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### **Features**

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Symmetrical design
  - Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
Ţ	Continuous Collector Current	$T_c = 25^{\circ}C$	110	
$I_{\rm C}$	Continuous Conector Current	$T_c = 80$ °C	90	Α
$I_{CM}$	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	385	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	150A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.85	2.25	V
$V_{CE(sat)}$		$I_C = 75A$ $T_j = 150$	$T_{j} = 150^{\circ}C$		2.25		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C =$	= 3mA	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V$ , $V_{CE} = 0V$				600	nA

**Dynamic Characteristics** 

·	Characteristic	Test Conditions	S	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$	$V_{GE} = 0V$ $V_{CE} = 25V$		4.4		
Coes	Output Capacitance				0.29		nF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			0.24		
$Q_{G}$	Gate charge	$V_{GE}=\pm 15V$ ; $V_{GE}=15V$	$V_{GE} = \pm 15V ; V_{CE} = 600V$ $I_{C} = 75A$		0.57		μС
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (25°C)		130		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			20		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600V$ $I_{\text{C}} = 75A$			300		
$T_{\mathrm{f}}$	Fall Time	$R_G = 2.2\Omega$	-		45		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Dec} = 600V$		150		ns
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15 V$ $V_{Bus} = 600 V$			35		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 75A$			350		
$T_{\rm f}$	Fall Time	$R_G = 2.2\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		3.4		mJ
Lon	Turn-on Switching Energy	$V_{Bus} = 600V$	$T_J = 150$ °C		8.5		1117
$E_{off}$	Turn-off Switching Energy	$I_C = 75A$ $R_G = 2.2\Omega$	$T_J = 25^{\circ}C$		4.2		mJ
Loff	Turn-on Switching Energy		$T_{\rm J} = 150^{\circ}{\rm C}$		7.2		1113
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V ; V_{Bu}$ $t_p \le 10 \mu s ; T_j = 1$			300		A

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_j = 25^{\circ}C$			250	μΑ
$I_F$	DC Forward Current		$Tc = 80^{\circ}C$		90		Α
$V_{\mathrm{F}}$	Diodo Forward Voltago	ode Forward Voltage $ \begin{aligned} I_F &= 75A \\ V_{GE} &= 0V \end{aligned} $	$T_i = 25^{\circ}C$		1.7	2.2	V
<b>v</b> F	Diode Polward Voltage		$T_{i} = 150^{\circ}C$		1.65		v
t <sub>rr</sub>	Reverse Recovery Time	T	$T_j = 25$ °C		155		ns
·rr			$T_{j} = 150^{\circ}C$		300		113
$Q_{rr}$	Reverse Recovery Charge	$I_F = 75A$ $V_R = 600V$	$T_j = 25$ °C		7.3		μС
Qrr		$di/dt = 1900A/\mu s$		$T_{j} = 150^{\circ}C$		15.2	
$E_{r}$	Reverse Recovery Energy		$T_j = 25$ °C		2.6		mJ
			$T_{\rm j} = 150^{\circ}{\rm C}$		5.5		1117



### Thermal and package characteristics

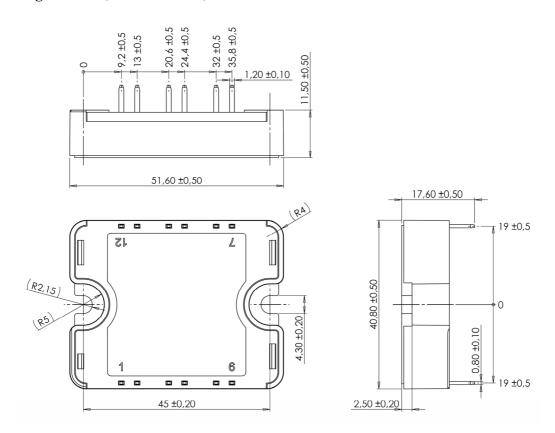
Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.39	°C/W
T <sub>th</sub> JC			Diode			0.62	C/ VV
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range			-40		175	
$T_{STG}$	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

### Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C	5°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
ΔΒ/Β		T <sub>C</sub> =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$
 
$$R_T: \text{ Thermistor value at T}$$

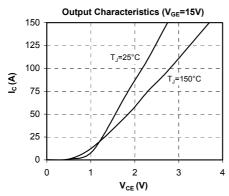
### SP1 Package outline (dimensions in mm)

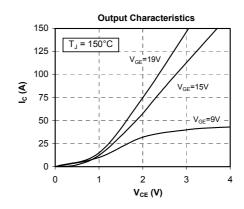


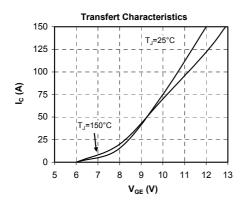
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

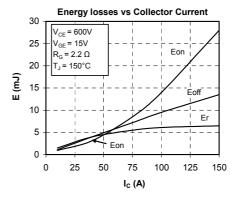


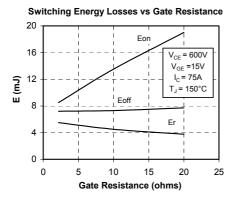
### **Typical Performance Curve**

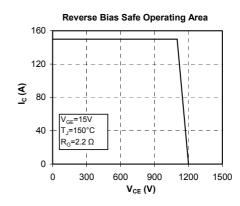


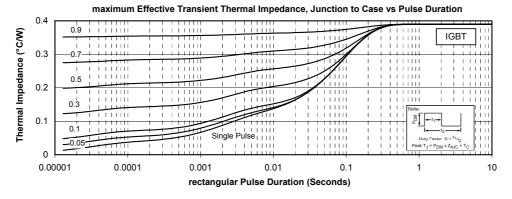




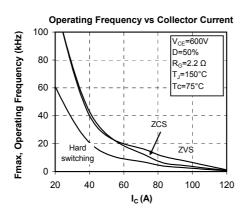


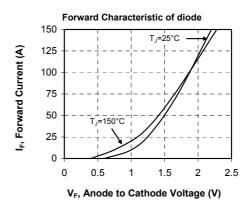


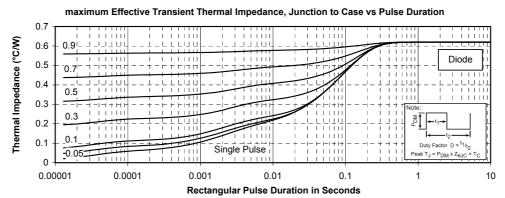












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